

METHOD OF MANUFACTURING SEMICONDUCTOR DEVICE, SUBSTRATE PROCESSING APPARATUS, AND PROGRAM

ABSTRACT

There is included forming a film containing a predetermined element, oxygen, and nitrogen on the substrate by performing a cycle a predetermined number of times, the cycle including: (a) supplying a first precursor containing the predetermined element to the substrate; (b) supplying a second precursor having a molecular structure different from a molecular structure of the first precursor and containing the predetermined element and oxygen; (c) supplying an oxidizing agent to the substrate; and (d) supplying a nitriding agent to the substrate.

Fig. 4